

	Typ	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRL S	1	1	("4911761").PN.	USPAT; EPO; JPO	2004/ 09/30 12:22			0
2	BRL S	2	32	("0061571" "0539074" "0539075" "0728148" "1066993" "1318160" "1845139" "2180274" "3005417" "3208157" "3437543" "3607549" "3632462" "3813311" "3871914" "3957531" "3964957" "3977926" "4017343" "4056428" "4079522" "4105468" "4159917" "4169807" "4323452" "4408960" "4426246" "4479849" "4519846" "4589926" "4633893" "4778532").PN.	USPAT	2004/ 09/30 12:21			0
3	BRL S	3	71	4911761.URPN.	USPAT	2004/ 09/30 12:21			0
4	BRL S	4	11	yamaguchi-kensuke.in.	USPAT; EPO; JPO	2004/ 09/30 12:23			0
5	BRL S	5	11 6	ishikawa-yoshinori.in.	USPAT; EPO; JPO	2004/ 09/30 12:23			0
6	BRL S	6	13	han-ki.in.	USPAT; EPO; JPO	2004/ 09/30 12:23			0
7	BRL S	7	13 7	4 5 6	USPAT; EPO; JPO	2004/ 09/30 12:23			0
8	BRL S	8	12	7 and (wafer substrate)	USPAT; EPO; JPO	2004/ 09/30 12:27			0
9	BRL S	9	1	6779534.pn.	USPAT; EPO; JPO	2004/ 09/30 12:32			0

	Type	Ln #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
10	BR S	L 10	64 9	34/463,487,506,498,467,459,44.ccls.	USPAT; EPO; JPO	2004/ 09/30 12:32			0
11	BR S	L 11	58	10 and (wafer substrate)	USPAT; EPO; JPO	2004/ 09/30 12:32			0
12	BR S	L 12	17 5	34/487.ccls.	USPAT; EPO; JPO	2004/ 09/30 12:33			0
13	BR S	L 13	13	12 and (wafer substrate)	USPAT; EPO; JPO	2004/ 09/30 12:33			0
14	BR S	L 14	12	10 and 134/902.ccls.	USPAT; EPO; JPO	2004/ 09/30 12:34			0
15	BR S	L 15	25 77	10 134/902.ccls.	USPAT; EPO; JPO	2004/ 09/30 12:34			0
16	BR S	L 16	76 9	(dry\$3 with (wafer substrate)) and (nitrogen inert) and (iospropyl ipa)	USPAT; EPO; JPO	2004/ 09/30 12:35			0
17	BR S	L 17	10 5	16 and ((direct guide vane) with (fluid nitrogen inert ipa isopropyl))	USPAT; EPO; JPO	2004/ 09/30 12:36			0
18	BR S	L 18	9	17 and ((direct guide vane) with (perforation hole diameter))	USPAT; EPO; JPO	2004/ 09/30 12:37			0

	Document ID	Issue Date	Title	Current OR	Current XRef	Inventor
1	US 6785982 B2	2004 0907	Drying apparatus and method for drying coated webs	34/463	34/465; 34/633	Yonkoski, Roger K. et al.
2	US 6748672 B2	2004 0615	Wafer dryers for Semiconductor cleaning apparatuses	34/630	134/902; 34/323; 34/487; 34/614	Lee, Sung-Hee et al.
3	US 6745494 B2	2004 0608	Method and apparatus for processing wafers under pressure	34/410	34/444; 34/467; 34/72	Bergman, Eric J. et al.
4	US 6742281 B2	2004 0601	Apparatus for drying semiconductor wafer using vapor dry method	34/366	34/236; 34/443; 34/467; 34/95	Shin, Myung-Hwan et al.
5	US 6729041 B2	2004 0504	Substrate processing apparatus and substrate processing method	34/444	34/218; 34/558; 34/568; 34/570; 34/74	Shindo, Naoki et al.
6	US 6725565 B2	2004 0427	Method for vacuum drying of substrate	34/266	257/E21.252; 257/E21.256; 34/406; 34/467; 34/92; 438/906	Harano, Riichiro et al.
7	US 6722056 B2	2004 0420	Drying vapor generation	34/381	257/E21.228; 34/179; 34/181; 34/444; 34/467; 34/480; 34/524	Myland, Lawrence J.
8	US RE38412 E	2004 0203	Coated substrate drying system with magnetic particle orientation	34/248	34/421; 34/463; 34/469; 34/73	Munter, John D. et al.

	Document ID	Issue Date	Title	Current OR	Current XRef	Inventor
9	US 6681499 B2	2004 0127	Substrate drying method for use with a surface tension effect dryer with porous vessel walls	34/467	134/95.2; 34/418	Scranton, Dana et al.
10	US 6668844 B2	2003 1230	Systems and methods for processing workpieces	134/155	134/137; 134/186; 134/30; 134/33; 134/902; 134/99.1; 34/165; 34/279; 34/288; 34/397; 34/444	Lund, Eric et al.
11	US 6649883 B2	2003 1118	Method of calibrating a semiconductor wafer drying apparatus	219/494	34/467	Iwamoto, Yoshio et al.
12	US 6647641 B1	2003 1118	Device and method for the treatment of substrates in a fluid container	34/451	134/902; 34/467; 34/614; 414/937; 414/938	Weber, Martin
13	US 6615510 B2	2003 0909	Wafer drying apparatus and method	34/448	34/218; 34/348; 34/444; 34/487; 34/630	Jones, Oliver David et al.
14	US 6589359 B2	2003 0708	Cleaning method and cleaning apparatus for substrate	134/26	134/102.1; 134/137; 134/153; 134/198; 134/2; 134/30; 134/33; 134/34; 134/42; 134/902; 134/95.1; 134/95.3; 34/443; 34/448; 34/467	Kamikawa, Yuji et al.

	Document ID	Issue Date	Title	Current OR	Current XRef	Inventor
15	US 6553689 B2	2003 0429	Vapor collection method and apparatus	34/444	162/204; 34/416; 34/445; 34/448; 34/468; 34/630; 34/631	Jain, Nirmal K. et al.
16	US 6550158 B2	2003 0422	Substrate handling chamber	34/451	34/404; 34/406; 34/409; 34/467; 34/487; 414/939	Doley, Allan et al.
17	US 6543156 B2	2003 0408	Method and apparatus for high-pressure wafer processing and drying	34/410	34/444; 34/467; 34/72	Bergman, Eric J. et al.
18	US 6533872 B1	2003 0318	Method and arrangement for drying substrates after treatment in a liquid	134/30	134/26; 134/32; 134/902; 34/443; 34/444; 34/498	Leenaars, Adriaan F. M. et al.
19	US 6519869 B2	2003 0218	Method and apparatus for drying semiconductor wafers	34/487	34/448; 34/470; 34/509; 34/632; 34/68; 34/74	Peng, Fu-Sheng
20	US 6511708 B1	2003 0128	Controlling float height of moving substrate over curved plate	427/372.2	34/448; 34/449; 34/459; 34/460; 427/398.1; 427/414.1	Kolb, William Blake et al.
21	US 6508014 B2	2003 0121	Method of drying substrates	34/467	257/E21.228; 34/402; 34/409; 34/474	Arndt, Russell H. et al.

	Document ID	Issue Date	Title	Current OR	Current XRef	Inventor
22	US 6505417 B2	2003 0114	Method for controlling airflow on a backside of a semiconductor wafer during spin processing	34/509	118/320; 118/500; 34/360; 34/364; 34/487; 34/498	Pascal, Roy Winston et al.
23	US 6473996 B1	2002 1105	Load port system for substrate processing system, and method of processing substrate	34/417	34/242; 34/487; 414/217; 414/937; 414/940	Tokunaga, Kenji
24	US 6449873 B1	2002 0917	Apparatus and method for dry cleaning of substrates using clusters	34/448	134/198; 134/37; 134/7; 134/902; 34/218; 34/232; 34/467; 34/487; 34/510; 34/516; 451/38; 451/39	Yoon, Deok-Joo et al.
25	US 6446358 B1	2002 0910	Drying nozzle and drying device and cleaning device using the same	34/611	34/230; 34/232; 34/419; 34/422; 34/444; 34/623; 34/629; 34/641; 34/69	Mitsumori, Kenichi et al.